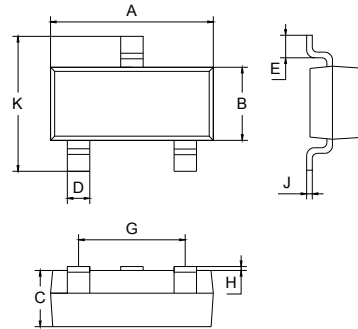
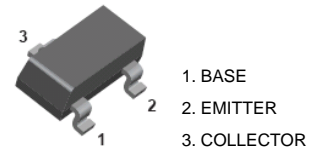


### Features

- Epitaxial planar die construction.
- Complementary NPN type available (MMBT4401).
- Also available in lead free version.
- Ideal for medium power amplification and switching.

### Applications

- Ideal for medium power amplification and switching.



SOT-23		
Dim	Min	Max
A	2.70	3.10
B	1.10	1.50
C	1.0 Typical	
D	0.4 Typical	
E	0.35	0.48
G	1.80	2.00
H	0.02	0.1
J	0.1 Typical	
K	2.20	2.60
All Dimensions in mm		

### ORDERING INFORMATION

Type No.	Marking	Package Code
MMBT4403	2T	SOT-23

### MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

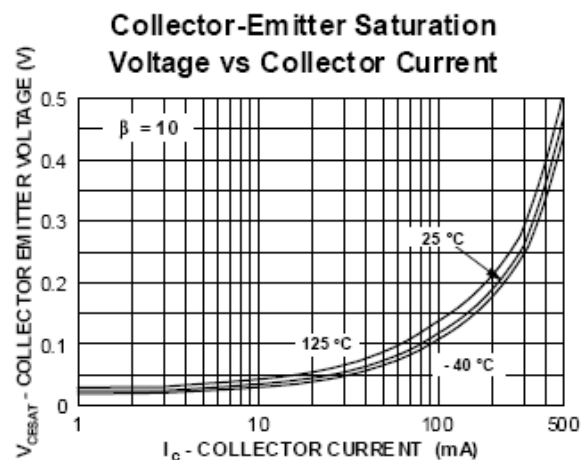
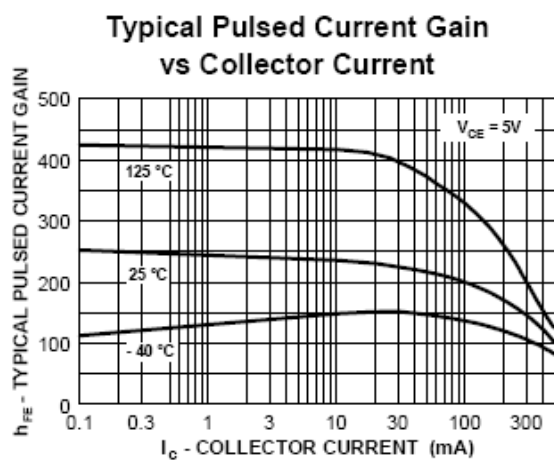
Symbol	Parameter	Value	UNIT
$V_{CBO}$	collector-base voltage	-40	V
$V_{CEO}$	collector-emitter voltage	-40	V
$V_{EBO}$	emitter-base voltage	-5	V
$I_C$	collector current (DC)	-0.6	A
$P_C$	Collector dissipation	0.35	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	$^\circ\text{C}/\text{W}$
$T_J, T_{stg}$	junction and storage temperature	-55 to +150	$^\circ\text{C}$

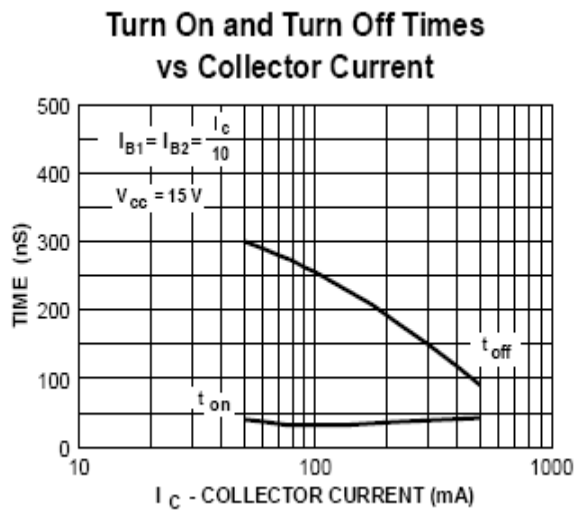
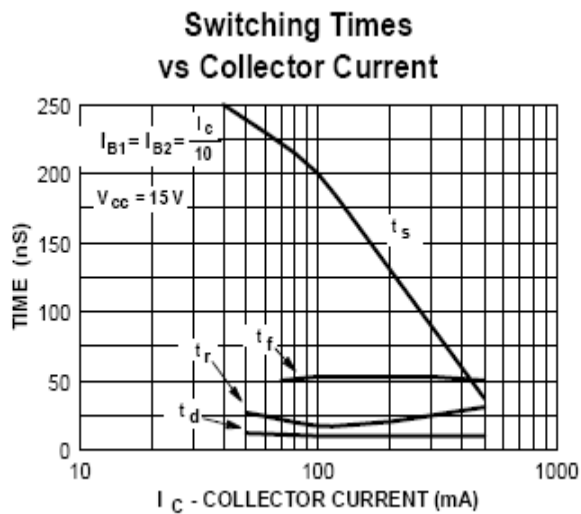
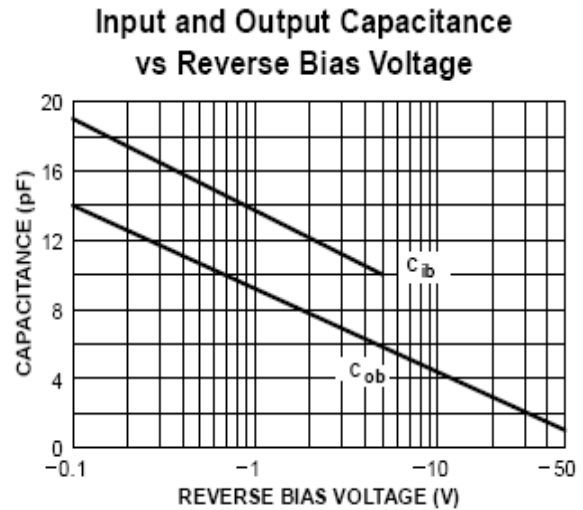
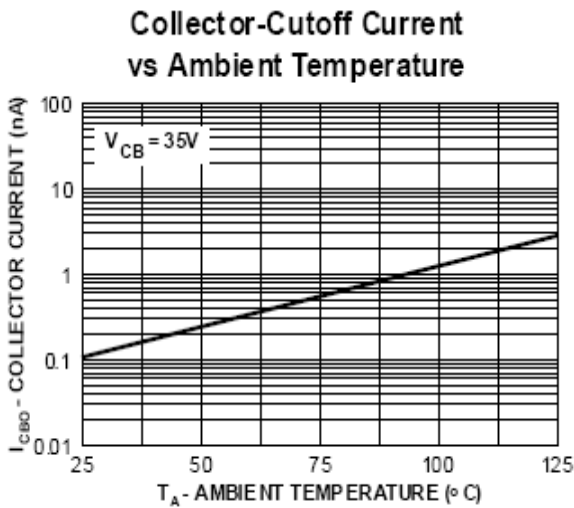
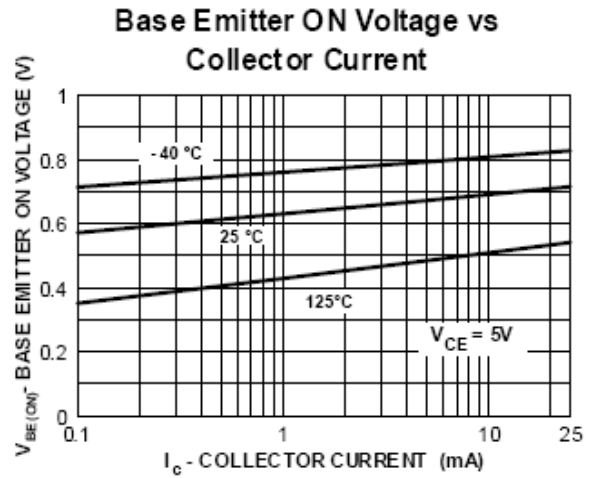
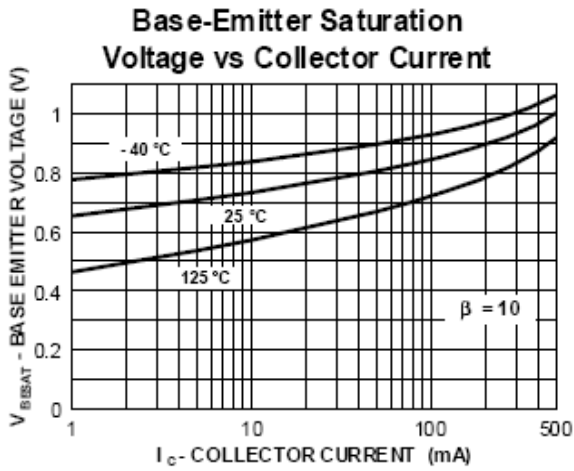


**ELECTRICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified**

Symbol	Parameter	Test conditions	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-100\mu\text{A}, I_E=0$	-40		
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-1\text{mA}, I_B=0$	-40		
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-100\mu\text{A}, I_C=0$	-5		
$I_{CEX}$	collector cut-off current	$V_{CE}=-35\text{V}, V_{BE}=0.4\text{V}$		-0.1	$\mu\text{A}$
$I_{BL}$	Base cut-off current	$V_{CE}=-35\text{V}, V_{BE}=-0.4\text{V}$		-0.1	$\mu\text{A}$
$h_{FE}$	DC current gain	$V_{CE} = -1\text{V}; I_C = -0.1\text{mA}$ $V_{CE} = -1\text{V}; I_C = -1\text{mA}$ $V_{CE} = -1\text{V}; I_C = -10\text{mA}$ $V_{CE} = -2\text{V}; I_C = -150\text{mA}$ $V_{CE} = -2\text{V}; I_C = -500\text{mA}$	30 60 100 100 20	300	
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$	-	-0.4 -0.75	V
$V_{BE(sat)}$	base-emitter saturation voltage	$I_C = -150\text{mA}; I_B = -15\text{mA}$ $I_C = -500\text{mA}; I_B = -50\text{mA}$	-0.75	-0.95 -1.3	V
$f_T$	transition frequency	$I_C = -20\text{mA}; V_{CE} = -10\text{V}; f = 100\text{MHz}$	200	-	MHz

**TYPICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified**





Device	Package	Shipping
MMBT4403	SOT-23	3000/Tape&Reel